DIGITRON SEMICONDUCTORS

MCR264-4 - MCR264-12

SILICON CONTROLLED RECTIFIERS

THYRISTORS

Available Non-RoHS (standard) or RoHS compliant (add PBF suffix). Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	•	Symbol	Value	Unit
Peak Repetitive Forward and Reverse Blocking Voltage ⁽¹⁾ ($T_1 = 25$ to 125°C, Gate Open)	MCR264-4 MCR264-6 MCR264-8 MCR264-10 MCR264-12	V _{drm} V _{rrm}	200 400 600 800 1000	Volts
Forward Current (T _c = 80°C) (All Conduction Angles)		$I_{T(RMS)} \\ I_{T(AV)}$	40 25	Amps
Peak Non-Repetitive Surge Current – 8.3ms(1/2 Cycle, Sine Wave)1.5ms		I _{TSM}	400 450	Amps
Forward Peak Gate Power		Р _{GM}	20	Watts
Forward Average Gate Power		P _{G(AV)}	0.5	Watt
Forward Peak Gate Current (300µs, 120PPS)		I_{GM}	2	Amps
Operating Junction Temperature Range		T ₃	-40 to +125	°C
Storage Temperature Range		T _{stg}	-40 to +150	°C

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

These devices are rated for use in applications subject to high surge conditions. Care must be taken to ensure proper heat sinking when the device is to be used at high sustained currents.

THERMAL CHARACTERISTICS

Characteristics	Symbol	Мах	Unit
Thermal Resistance, Junction to Case	R _{θJC}	1	°C/W
Thermal Resistance, Junction to Ambient	R _{θJA}	60	°C/W

ELECTRICAL CHARACTERISTICS ($T_c = 25^{\circ}C$ unless otherwise noted.

Characteristics		Symbol	Min	Тур	Мах	Unit
Peak Forward or Reverse Blocking Current (V _{AK} = Rated V _{DRM} or V _{RRM} , Gate Open)	T ₁ = 25°C T ₁ = 125°C	I _{drm} , I _{rrm}			10 2	μA mA
Forward "On" Voltage ⁽¹⁾ (I _{TM} = 80A)		V _{TM}	-	1.4	2	Volts
Gate Trigger Current (Continuous dc) (Anode Voltage = 12 Vdc, R_L = 100 Ohms, T_C = -40°C)		I _{GT}		15 30	50 90	mA
Gate Trigger Voltage (Continuous dc) (Anode Voltage = 12 Vdc, R_L = 100 Ohms)		V _{GT}	-	1	1.5	Volts
Gate Non-Trigger Voltage (Anode Voltage = Rated V_{DRM} , R_L = 100 Ohms, T_J = 125°C)		V _{GD}	0.2	-	-	Volts
Holding Current (Anode Voltage = 12 Vdc)		I _H	-	30	60	mA
Turn-On Time (I_{TM} = 40 A, I_{GT} = 60 mAdc)		t _{gt}	-	1.5	-	μs
Critical Rate-of-Rise of Off-State Voltage (Gate Open, V _D = Rated V _{DRM} , Exponential Waveform)		dv/dt	-	50	-	V/µs

1. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

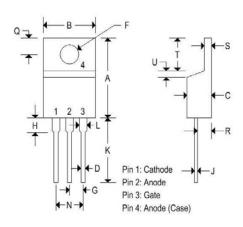
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MECHANICAL CHARACTERISTICS

Case	TO-220AB
Marking	Alpha-numeric
Pin out	See below



	TO-220AB				
	Inches		Millim	neters	
	Min	Max	Min	Max	
Α	0.575	0.620	14.600	15.750	
В	0.380	0.405	9.650	10.290	
С	0.160	0.190	4.060	4.820	
D	0.025	0.035	0.640	0.890	
F	0.142	0.147	3.610	3.730	
G	0.095	0.105	2.410	2.670	
Н	0.110	0.155	2.790	3.930	
J	0.014	0.022	0.360	0.560	
К	0.500	0.562	12.700	14.270	
L	0.045	0.055	1.140	1.390	
Ν	0.190	0.210	4.830	5.330	
Q	0.100	0.120	2.540	3.040	
R	0.080	0.110	2.040	2.790	
S	0.045	0.055	1.140	1.390	
T	0.235	0.255	5.970	6.480	
U	-	0.050	-	1.270	
٧	0.045	12	1.140	-	
Ζ		0.080	1	2.030	

FIGURE 1 — AVERAGE CURRENT DERATING

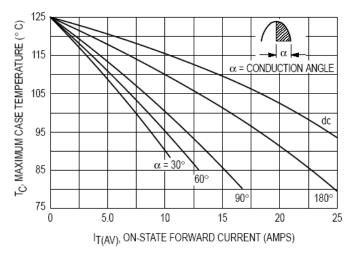
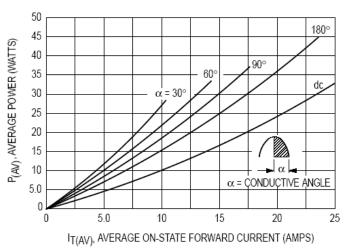


FIGURE 2 — MAXIMUM ON-STATE POWER DISSIPATION



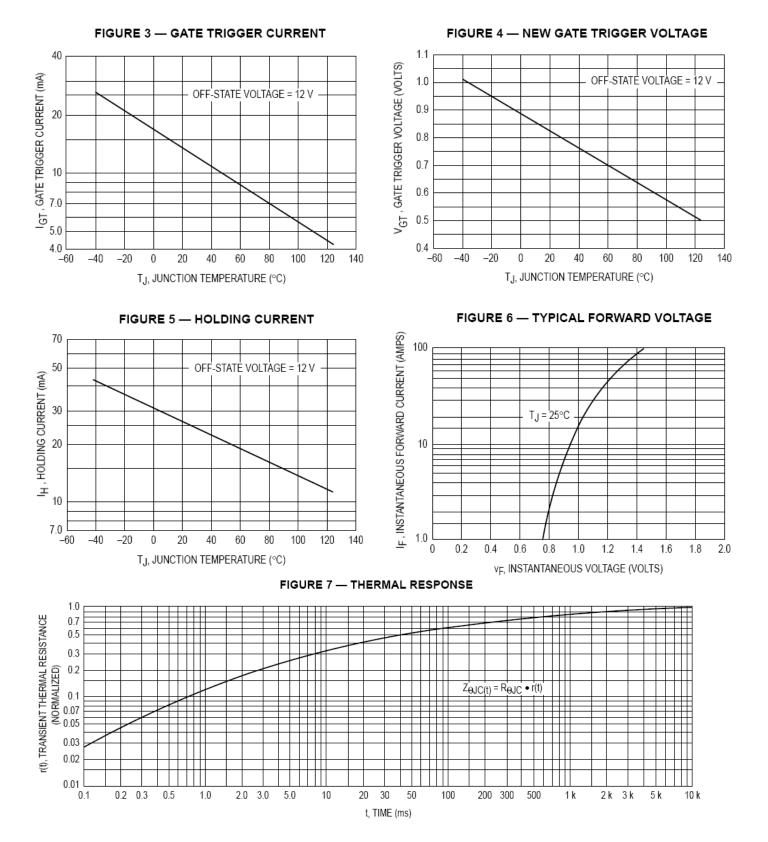
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